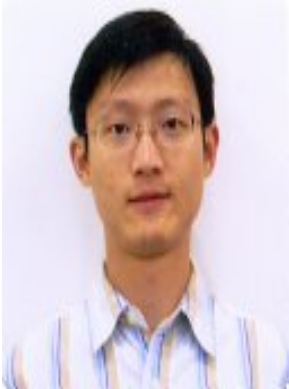

Berry-Connection Polarizability and Third-Order Hall Effect

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Abstract:

Hall effect has a central position in condensed matter physics. The various Hall effects offer standard tools for material characterization, and understanding their microscopic mechanisms often unravels nontrivial properties of electrons in solids. One breakthrough twenty years ago is the recognition of the importance of geometric phase in anomalous Hall effect, i.e., the Hall effect in magnets without external magnetic field. Recently, the study has been extended to the nonlinear regime. I shall discuss our theoretical understanding of the second-order and the third-order anomalous Hall effect, and show that they reflect a new intrinsic band geometric quantity, the Berry-connection polarizability. We demonstrate the evaluation of this quantity from first-principles calculation for real materials, and experimental measurement of the third-Hall effect on MoTe₂, WTe₂, and TaIrTe₄ (by Gao Weibo group) obtained results consistent with theory.